



THE DATASHEET OF BSP19TA



SOT223 NPN SILICON PLAIN HIGH VOLTAGE TRANSISTOR

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FEATURES

- * High V_{CE0} – 350V
- * Low saturation voltage

COMPLEMENTARY TYPE – BSP16

PARTMARKING DETAIL – BSP19

ABSOLUTE MAXIMUM RATINGS

PARAMETER	
Collector-Base Voltage	
Collector-Emitter Voltage	
Emitter-Base Voltage	
Peak Pulse Current	
Continuous Collector Current	
Power Dissipation at $T_{amb}=25^{\circ}C$	
Operating and Storage Temperature Range	



ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	MIN	MAX
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	40	
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	35	
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5	
Collector Cut-Off Current	I_{CBO}		
Emitter Cut-Off Current	I_{EBO}		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		
Static Forward Current Transfer Ratio	h_{FE}	40	50
Transition Frequency	f_T	70	
Output Capacitance	C_{obo}		

*Measured under pulsed conditions. Pulse width and duty cycle dependent.
Spice parameter data is available upon request.
For typical characteristics graphs see FZT6

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